TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74ACT373P,TC74ACT373F,TC74ACT373FT

#### Octal D-Type Latch with 3-State Output

The TC74ACT373 is an advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

These 8-bit D-type latches are controlled by a latch enable (LE) and a output enable input  $(\overline{OE})$ .

When the  $(\overline{OE})$  input is high, the eight outputs are in a high impedance state.

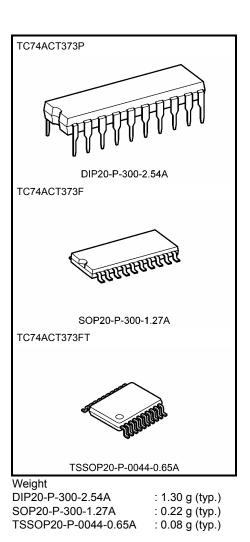
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### Features

- High speed:  $t_{pd} = 5.2 \text{ ns}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $ICC = 8 \mu A (max)$  at  $Ta = 25^{\circ}C$
- Compatible with TTL outputs: VIL = 0.8 V (max)

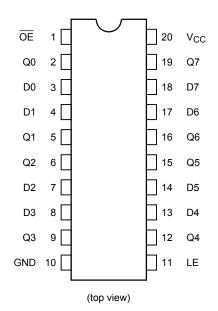
 $V_{IH} = 2.0 V (min)$ 

- Symmetrical output impedance:  $|I_{OH}| = I_{OL} = 24$  mA (min) Capability of driving 50  $\Omega$ transmission lines.
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with 74F373



# TOSHIBA

# **Pin Assignment**



# **IEC Logic Symbol**

0E <u>(1)</u> LE <u>(11)</u>	EN C1		
D0 (3) D1 (4) D2 (7) D3 (8) D4 (13) D5 (14) D5 (14) D6 (17) D7 (18)	1D	7 4	(2) Q0 (5) Q1 (6) Q2 (9) Q3 (12) Q4 (15) Q5 (16) Q6 (19) Q7

# Truth Table

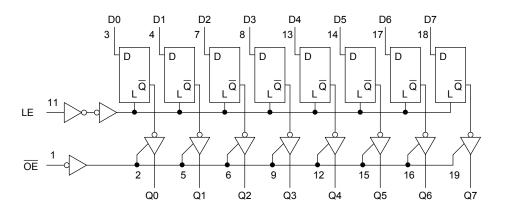
	Inputs	Output	
ŌE	LE	D	Q
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 $Q_n$ : Q outputs are latched at the time when the LE input is taken to a low logic level.

# System Diagram



#### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V
DC input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Input diode current	IIK	±20	mA
Output diode current	I <sub>ОК</sub>	±50	mA
DC output current	IOUT	±50	mA
DC V <sub>CC</sub> /ground current	Icc	±200	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5 to 5.5	V
Input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
Input rise and fall time	dt/dV	0 to 10	ns/V

## **Operating Ranges (Note)**

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol			Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit	
				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Onic	
High-level input voltage	VIH	_			4.5 to 5.5	2.0	_	_	2.0	_	V
Low-level input voltage	VIL		_			_	_	0.8	_	0.8	V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA		4.5	4.4	4.5	_	4.4	_	
High-level output voltage	V <sub>OH</sub>		I <sub>OH</sub> = −24 mA		4.5	3.94	—	—	3.80	—	V
			I <sub>OH</sub> = −75 mA	(Note)	5.5	_	—	—	3.85	—	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA		4.5	_	0.0	0.1	_	0.1	
Low-level output voltage	Vol		I <sub>OL</sub> = 24 mA		4.5	_	_	0.36	_	0.44	V
voluge			I <sub>OL</sub> = 75 mA	(Note)	5.5	—	—	—	—	1.65	
3-state output off-state current	I <sub>OZ</sub>	V <sub>IN</sub> = V <sub>IH</sub> V <sub>OUT</sub> = \	<sub>H</sub> or V <sub>IL</sub> / <sub>CC</sub> or GND		5.5	_	_	±0.5	_	±5.0	μΑ
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>C</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	-	_	±0.1	_	±1.0	μA
I <sub>CC</sub>	I <sub>CC</sub>	$V_{IN} = V_C$	<sub>C</sub> or GND		5.5	_	_	8.0	_	80.0	μA
Quiescent supply current	Ι <sub>C</sub>		Per input: $V_{IN}$ = 3.4 V Other input: $V_{CC}$ or GND			_	_	1.35	_	1.5	mA

Note: This spec indicates the capability of driving 50  $\Omega$  transmission lines.

One output should be tested at a time for a 10 ms maximum duration.

#### Timing Requirements (input: t<sub>r</sub> = t<sub>f</sub> = 3 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40 to 85°C	Unit
			V <sub>CC</sub> (V)	Limit	Limit	Limit	
Minimum pulse width (LE)	t <sub>w (H)</sub>	_	5.0 ± 0.5	_	5.0	5.0	ns
Minimum set-up time	ts	—	5.0 ± 0.5	_	2.0	2.0	ns
Minimum hold time	t <sub>h</sub>	-	5.0 ± 0.5		3.0	3.0	ns

#### AC Characteristics (C<sub>L</sub> = 50 pF, R<sub>L</sub> = 500 $\Omega$ , input: t<sub>r</sub> = t<sub>f</sub> = 3 ns)

Characteristics Sy	Symbol	Test Condition		Ta = 25°C			Ta −40 to	Unit	
	-,		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
Propagation delay time (LE-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	_	5.0 ± 0.5	_	5.8	9.2	1.0	10.5	ns
Propagation delay time (D-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	_	5.0 ± 0.5	_	5.9	9.6	1.0	11.0	ns
Output enable time	t <sub>pZL</sub> t <sub>pZH</sub>	_	5.0 ± 0.5	_	6.5	10.5	1.0	12.0	ns
Output disable time	t <sub>pLZ</sub> t <sub>pHZ</sub>	_	5.0 ± 0.5	_	5.5	7.8	1.0	9.0	ns
Input capacitance	C <sub>IN</sub>	_		_	5	10	_	10	pF
Output capacitance	C <sub>OUT</sub>	—		_	10	_	—	_	pF
Power dissipation capacitance	C <sub>PD</sub>		(Note)	_	32	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per latch)

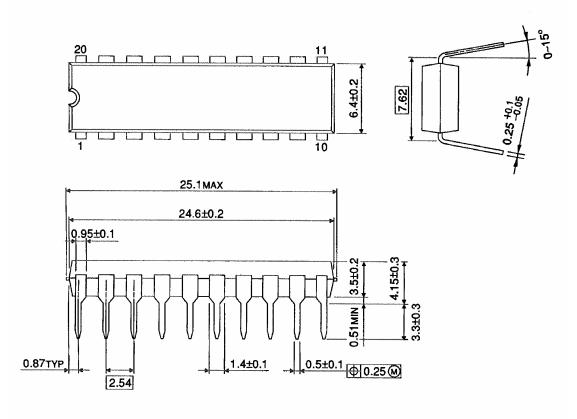
And the total C<sub>PD</sub> when n pcs. of F/F operate can be gained by the following equation:

C<sub>PD</sub> (total) = 20 + 12·n

## Package Dimensions

DIP20-P-300-2.54A

Unit : mm



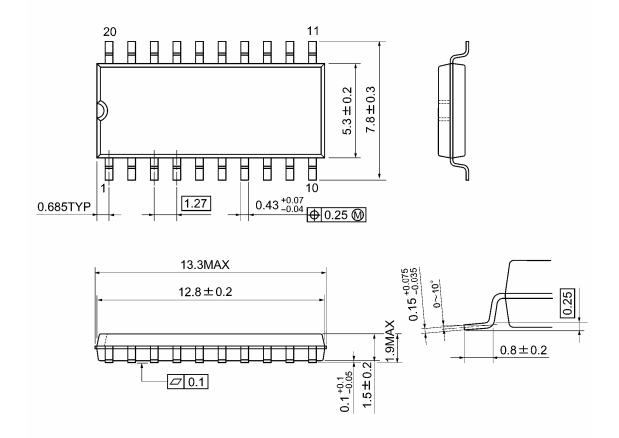
Weight: 1.30 g (typ.)

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## **Package Dimensions**

SOP20-P-300-1.27A

Unit: mm



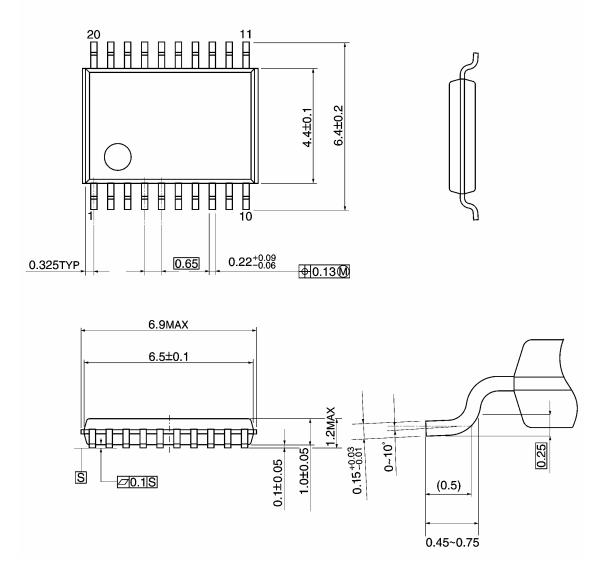
Weight: 0.22 g (typ.)

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## **Package Dimensions**

TSSOP20-P-0044-0.65A

Unit: mm



Weight: 0.08 g (typ.)

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20070701-EN GENERAL

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